

## Electronic supplementary information (ESI) for

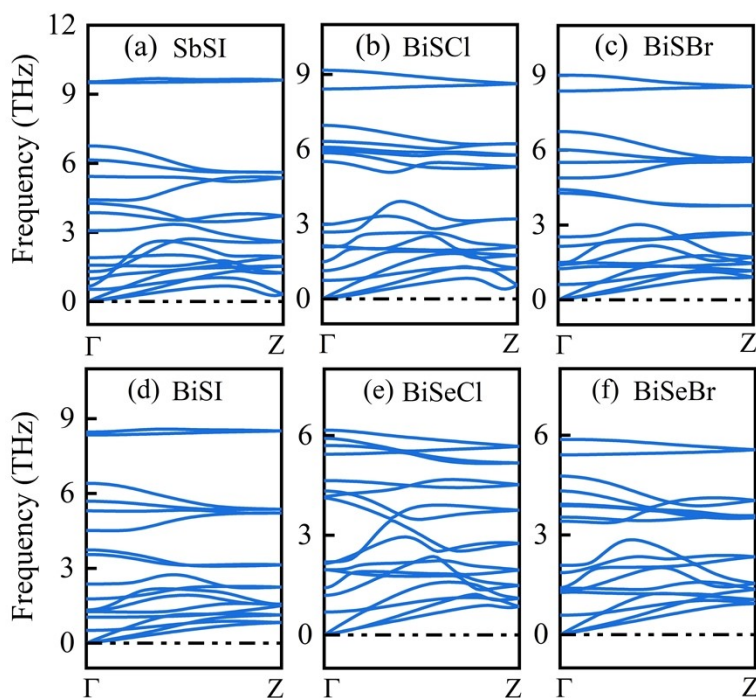
### 1D group V-VI-VII ternary nanowires: moderate band gaps, easy to exfoliate from bulk, and unexpected ferroelectricity†

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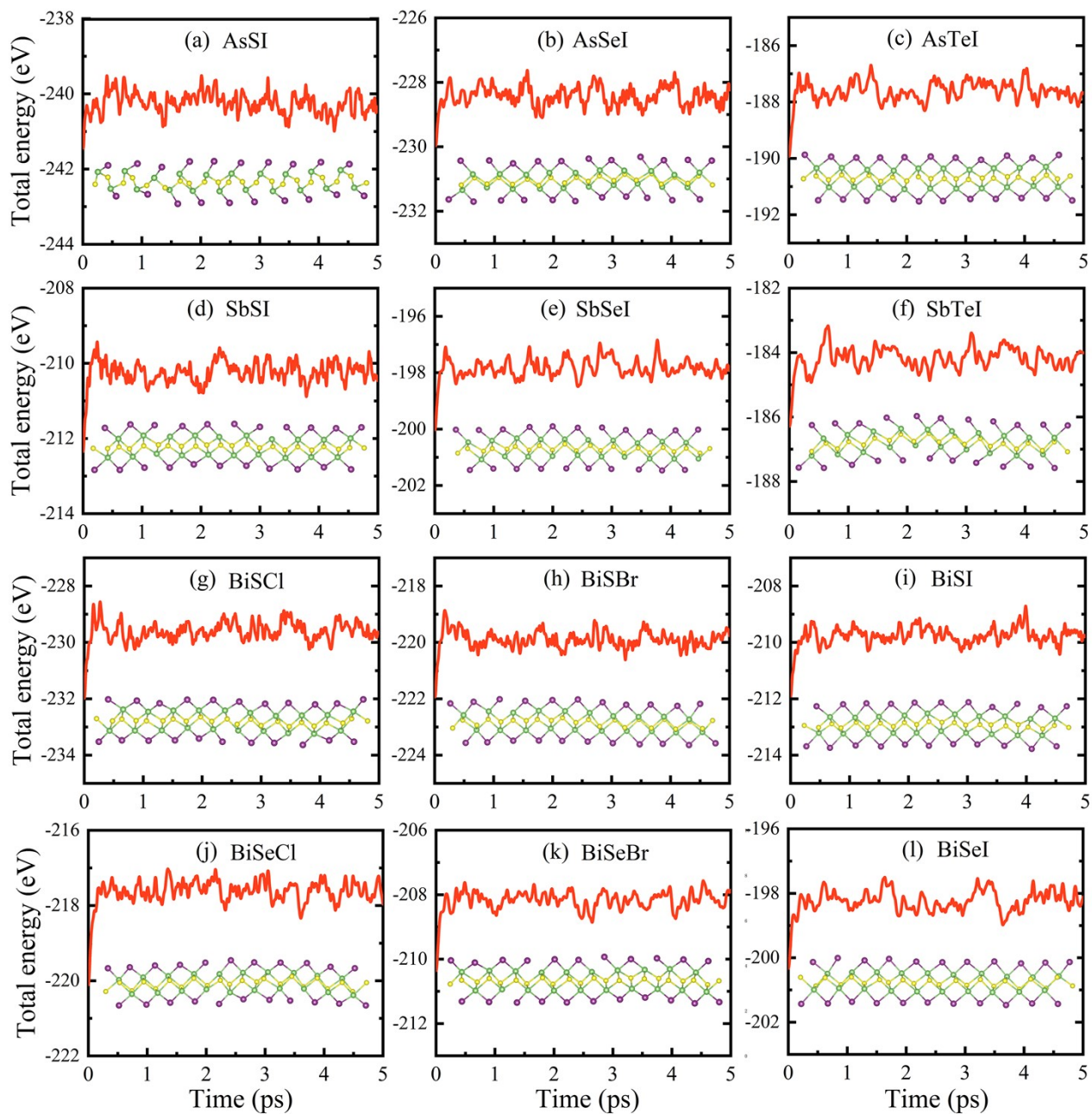
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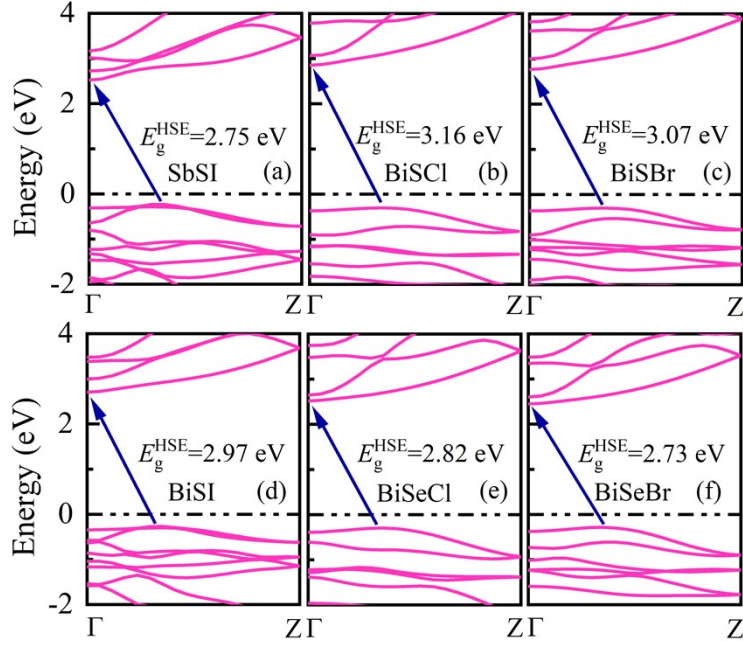
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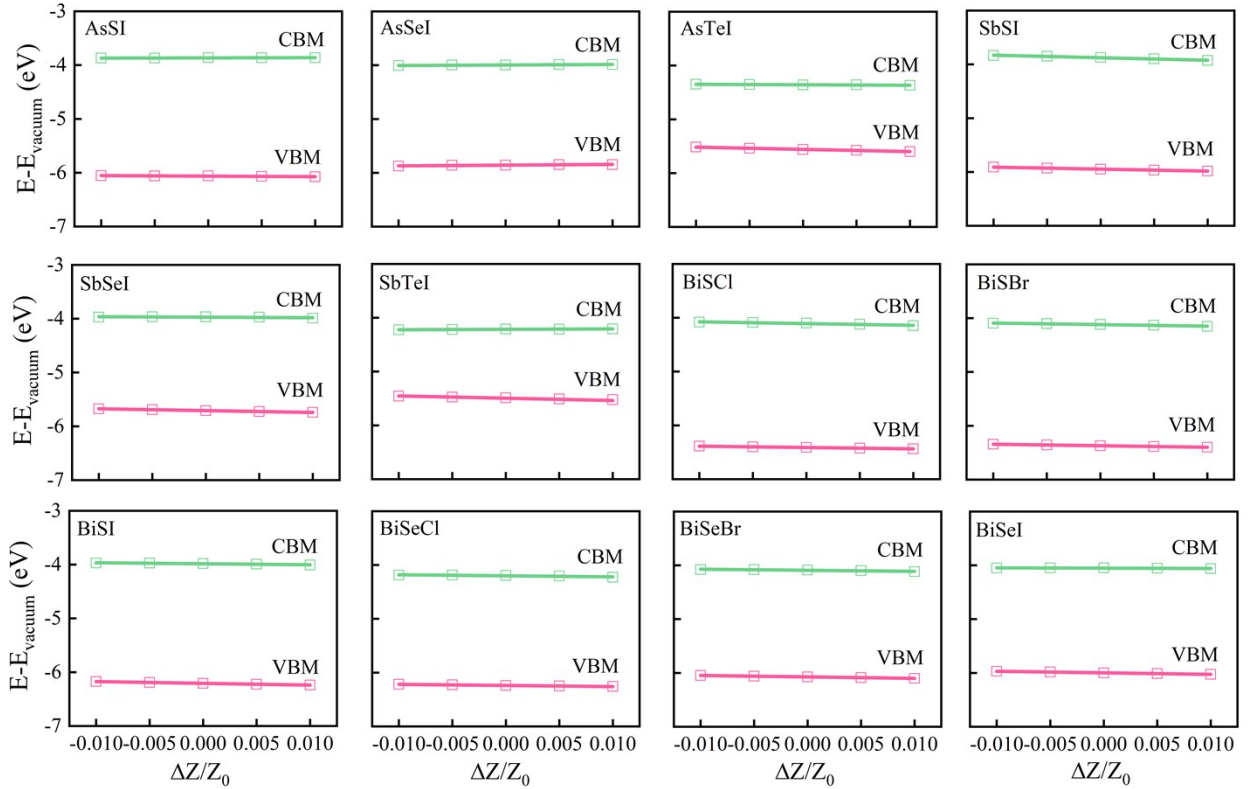
**Fig. S1.** The phonon dispersion spectra of partial 1D  $X^V Y^{VI} Z^{VII}$  nanowires: (a) SbSI, (b) BiSbCl, (c) BiSbBr, (d) BiSI, (e) BiSeCl, and (f) BiSeBr.



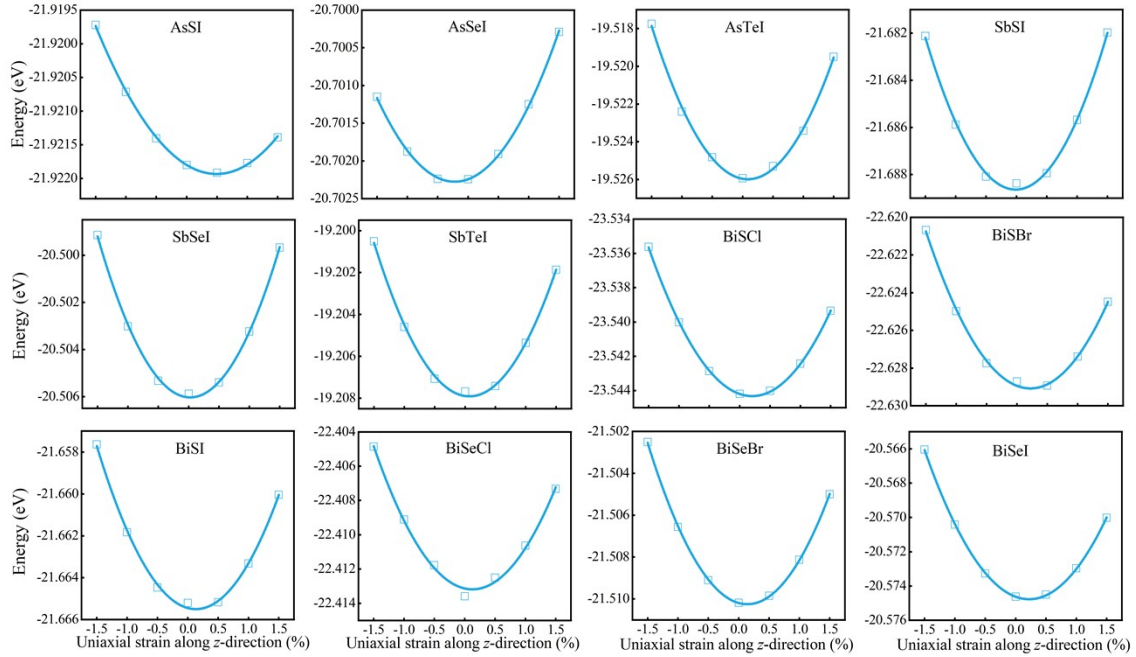
**Fig. S2.** The evolution of energies from AIMD simulations at 300 K of 1D  $X^{\text{V}}Y^{\text{VI}}Z^{\text{VII}}$  nanowires. The insets present the snapshot of atomic structure after 5 ps.



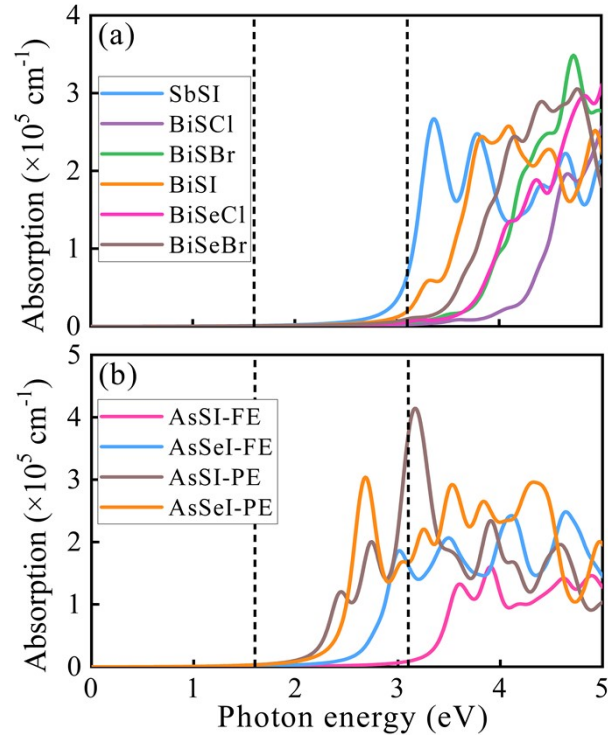
**Fig. S3.** The HSE06 band structures of partial 1D  $X^V Y^VI Z^VII$ : (a) SbSI, (b) BiSbCl, (c) BiSbBr, (d) BiSI, (e) BiSeCl, and (f) BiSeBr. The Fermi level is set to 0.



**Fig. S4.** Evaluations of band edges of nanowires 1D  $X^V Y^VI Z^VII$  ( $X=As, Sb, Bi$ ;  $Y=S, Se, Te$ ;  $Z=Cl, Br, I$ ) relative to vacuum level with respect to strains along the chain direction. The slope is the deformation potential  $E_1$ .



**Fig. S5.** The total energy of 1D  $X^V Y^VI Z^VII$  ( $X=As, Sb, Bi$ ;  $Y=S, Se, Te$ ;  $Z=Cl, Br, I$ ) nanowires as a function of the uniaxial strain applied along the chain direction.



**Fig. S6.** (a) Calculated absorption coefficients of the partial 1D  $X^V Y^VI Z^VII$  nanowires at the HSE06 level: SbSI, BiSbI, BiBrI, BiSI, BiSeCl, and BiSeBr. (b) The comparisons of absorption coefficients between the ferroelectric (FE) and paraelectric (PE) phases for 1D AsSI and AsSeI nanowires. The vertical dashed lines represent the visible region.